

FORMATION OF SILICON OXIDE COATING FILM

FORMATION OF SILICON OXIDE COATING FILM

Patent Number: JP60065712
Publication date: 1985-04-15
Inventor(s): HAYAMA NORIYUKI; others: 03
Applicant(s): TOSHIBA KK
Requested Patent: ☐ JP60065712
Application Number: JP19830172222 19830920
Priority Number(s):
IPC Classification: C01B33/113
EC Classification:
EC Classification:
Equivalents:

Abstract

PURPOSE: A substrate is coated with an organosilicon compound containing ultra-violet absorbing substances and sintered in an oxidative atmosphere as ultraviolet rays are irradiated to effect oxidation whereby good coating films of silicon oxide are formed at relatively low temperatures.

CONSTITUTION: A substrate is coated with an organosilicon compound containing an ultraviolet absorbing substance such as an organotitanium compound and placed in a heating furnace, then baked in an oxidative atmosphere at about 350 deg.C, as ultraviolet rays are irradiated to oxidize the organosilicon compound and form coating films of silicon oxide on the substrate. Thus, silicon oxide coating films used as optical interference films with high refractive index.